					P-6244 (3008-2-008003)		pplication Number	035,672 #S		
O P ENFORMATION DISCLOSURE CITATION (Use several sheets if necessary)					Applicant(s) WANG et al.					
OCT 2 9 201	2026 1026				Filing Date Group Art Unit 1765					
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MA		EP 1 143 493 A2	10/10/2001	EUROI	PE					
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(10)		Docket Number (Option P-6244 (3005-2-008003)	Application Number 10/035,672			
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